

Data Sheet

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Manufacturers of World Class Discrete Semiconductors

CBR10-J010 SERIES

SILICON BRIDGE RECTIFIER
10 AMPS, 100 THRU 1000 VOLTS

CASE CM

DESCRIPTION

The CENTRAL SEMICONDUCTOR CBR10-J010 Series types are Silicon Single Phase Full Wave Bridge Rectifiers designed for general purpose applications.

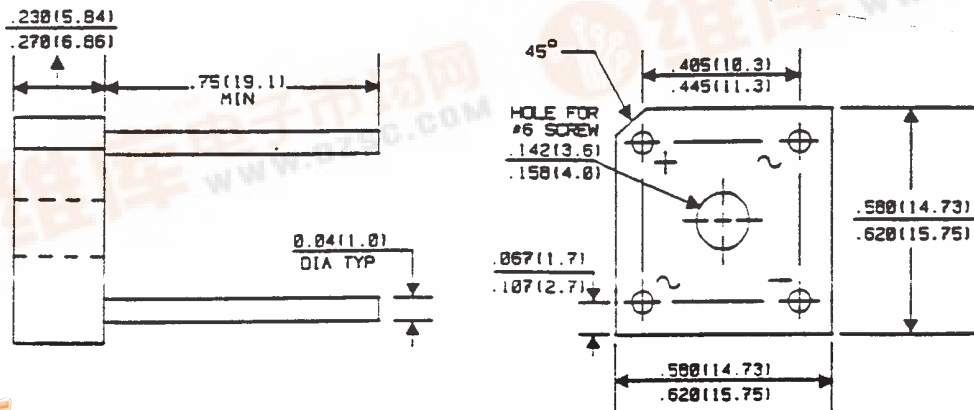
MAXIMUM RATINGS ($T_A = 50^\circ\text{C}$)

	SYMBOL	CBR10 -J010	CBR10 -J020	CBR10 -J040	CBR10 -J060	CBR10 -J080	CBR10 -J100	UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
DC Blocking Voltage	V_R	100	200	400	600	800	1000	V
RMS Reverse Voltage	$V_R(RMS)$	70	140	280	420	560	700	V
Average Forward Current *								
$T_C = 80^\circ\text{C}$	I_O			10				A
$T_A = 30^\circ\text{C}$	I_O			5.0				A
Peak Forward Surge Current	I_{FSM}			150				A
Operating and Storage								
Junction Temperature	T_J, T_{stg}			-65 to +150				$^\circ\text{C}$
Thermal Resistance	θ_{JC}			3.0				$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
V_F	$I_F = 5.0\text{A}$		1.2	V
I_R	$V_R = \text{Rated } V_{RRM}$		10	μA

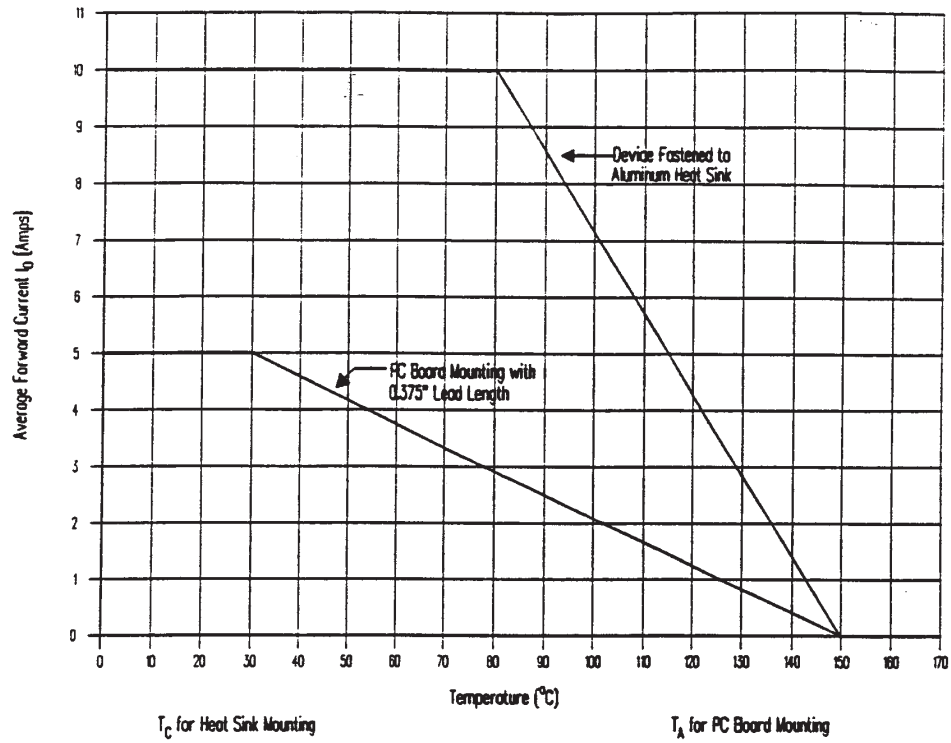
* SEE REVERSE FOR CURVE.



DIMENSIONS IN INCHES (mm).

Derating Curve for Average Forward Current

(60 Hz Resistive or Inductive Load)



Typical Instantaneous Forward

Characteristics Per Bridge Element

